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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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## Complete if Known

Application Number 10/699,574  
Filing Date October 31, 2003  
First Named Inventor Ge, et al.  
Art Unit 2826  
Examiner Name TSM03-0660  
Attorney Docket Number TSM03-0660

Sheet 1 of 5

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
MLT	1	US-4,072,974	02-07-1978	Ipi	
	2	US-4,631,803	12-30-1988	Hunter, et al.	
	3	US-5,013,681	05-07-1991	Godbey, et al.	
	4	US-5,024,723	08-18-1991	Goessele, et al.	
	5	US-5,213,986	05-25-1993	Pinker, et al.	
	6	US-5,374,584	12-20-1994	Bruel	
	7	US-5,447,884	09-05-1995	Fahey, et al.	
	8	US-5,461,250	10-24-1995	Burghartz, et al.	
	9	US-5,468,657	11-21-1995	Hsu	
	10	US-5,534,713	07-09-1996	Ismail, et al.	
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	36	US-6,410,938 B1	06-25-2002	Xiang	

Examiner  
Signature

Minhloan Tran

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/699,574
				Filing Date	October 31, 2003
				First Named Inventor	Ge, et al.
				Art Unit	<del>2811</del> 2826
				Examiner Name	<del>TBD</del> Minh Loan Tran
Sheet	2	of	5	Attorney Docket Number	TSM03-0660

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FOREIGN PATENT DOCUMENTS					
Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
	Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> ( <i>if known</i> )				
46 <u>MLT</u>	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation	—	

Examiner Signature	Minh loan Tran	Date Considered	1/05
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				Examiner Name	IBD Minhloan Tran
Sheet	3	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cita No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	2
MLT	47	ISMAIL, K., et al., "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letter, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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	55	MAITI, C.K., et al., "Film Growth and Material Parameters," Application of Silicon-Germanium Heterostructure, Institute of Physics Publishing, Ch. 2 (2001) pp. 32-42.	
	56	TIWARI, S., et al., "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," International Electron Device Meeting, (1997), pp. 939-941.	
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Examiner Signature	Minhloan Tran	Date Considered	1/05
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				Art Unit	2844 2826
				Examiner Name	TBD- Minhloan Tran
Sheet	4	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cita No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	P <sup>2</sup>
MLT	60	MATTHEWS, J.W., et al., "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
	61	SCHÜPPEN, A., et al., "Mesa and Planar SiGe-HBTs on MBE-Wafers," Journal of Materials Science: Materials in Electronics, Vol. 6, (1995), pp. 298-305.	
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	63	CURRENT, M.L., et al., "Atomic-Layer Cleaving and Non-Contact Thinning and Thickening for Fabrication of Laminated Electronic and Photonic Materials," 2001 Materials Research Society Spring Meeting (April 16-20, 2001).	
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Sheet	5	of	5
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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.

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